

# Smd General Purpose Transistor Npn Bc817 16 Bc817 25 Free Pdf Books

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## **SMD General Purpose Transistor (NPN) BC817-16/BC817-25 ...**

SMD General Purpose Transistor (NPN) Features • NPN Silicon Epitaxial Planar Transistor For Switching And Amplifier Applications • RoHS Compliance Mechanical Data Case: SOT-23, Plastic Package Terminals: Solderable Per MIL-STD-202G, Method 208 Weight: 0.008 Gram Marking Information BC817-16 BC17-25 BC817-40 Marking Code 6A 6B 6C Apr 18th, 2024

### **BC817-40W - 45 V, 0.5 A, General Purpose NPN Transistor**

\*Date Code Orientation And/or Overbar May Vary Depending Upon Manufacturing Location. ... Safe Operating Area 1 VCE (Vdc) 0.1 1 0.1 0.01 10 100 0.01 0.001 I C (A) Single Pulse Test @ TA = 25°C Thermal Limit 100 Ms 1 S 10 Ms 1 Ms. SC-70 (SOT-323) CASE 419 ISSUE P DATE 07 OCT 2021 SCALE 4 Mar 8th, 2024

### **2N4400 & 2N4401 Silicon NPN Transistor General Purpose ...**

2N4401 40 – 500 Output Admittance  $H_{oe}$  IC = 1mA, VCE = 10V, F = 1kHz 1.0 – 30  $\mu$ hos Switching Characteristics Delay Time Td VCC = 30V, VEB = 2V, IC = 150mA, IB1 = 15mA – – 15 Ns Rise Time Tr – – 20 Ns Storage Time Ts VCC = 30V, IC = 150mA, IB1 = IB2 = 15mA – – 225 Ns Fall Time Tf – – 30 Ns Note 1. Pulse Test: Pulse Width  $\leq$  ... Feb 5th, 2024

### **SMD General Purpose Transistor (PNP) MMBT2907A**

Marking Code 2F -VCEO Collector-Emitter Voltage (Open Base) 60 V -VCBO Collector-Base Voltage (Open Emitter) 60 V -VEBO Emitter-Base Voltage (Open Collector) 5.0 V -IC Collector Current (D.C) 600 MA Ptot Power Dissipation Above 25°C 250 MW FT

Transition Frequency At  $F = 100\text{MHz}$   $200\text{ MHz}$   $-I_C = 50\text{mA}$ ,  $-V_{CE} = 20\text{V}$  Apr 18th, 2024

### **MJE13007 Switch-mode NPN Bipolar Power Transistor**

Power Transistor For Switching Power Supply Applications The MJE13007 Is Designed For High-voltage, High-speed Power Switching Inductive Circuits Where Fall Time Is Critical. It Is Particularly Suited For 115 And 220 V Switch-mode Applications Such As Switching Regulators, Inverters, Jan 22th, 2024

### **High Voltage Transistor BF393 NPN Silicon**

BF393 [Http://onsemi.com](http://onsemi.com) 3 Figure 1. DC Current Gain  $I_C$ , COLLECTOR CURRENT (mA) 200 1.0 2.0 3.0 5.0 7.0 10 2 Mar 20th, 2024

### **Npn Bipolar Junction Transistor**

EE 436 BJT Currents - 9 External (terminal) Currents. All Currents Depend On  $V_{BE}$  In Exactly The Same Way. Although It Is A Messy Exponential, They Are All Tracking Together. It Makes Sense To Look At The Ratios: Forward Current Jan 15th, 2024

### **MPSA44 NPN High-voltage Transistor**

NXP Semiconductors Product Data Sheet NPN High-voltage Transistor MPSA44 DATA SHEET STATUS Notes 1. Please Consult The Most Recently Issued Document Before Initiating Or Completing A Design. 2. The Product Status Of Device(s) Described In This Document May Have Changed Since This Document Was Published And May Differ In Case Of Multiple Devices. Apr 16th, 2024

### **MJE800/801/802/803 NPN Epitaxial Silicon Darlington Transistor**

©2001 Fairchild Semiconductor Corporation Rev. A1, February 2001

MJE800/801/802/803 ... Cross-reference Search Technical Information Buy Products Technical Support My Fairchild Company MJE800 NP Mar 4th, 2024

### **2N4401 NPN Switching Transistor - ElectroSchematics.com**

Jul 02, 2013 · NPN Switching Transistor 2N4401 PACKAGE OUTLINE UNIT A OUTLINE REFERENCES VERSION EUROPEAN PROJECTION ISSUE DATE IEC JEDEC JEITA Mm 5.2 5.0 B 0.48 0.40 C 0.45 0.38 D 4.8 4.4 D 1.7 1.4 E 4.2 3.6 L 14.5 12.7 E 2.54 E1 1.27 L1 (1) Max. 2.5 B1 0.66 0.55 DIMENSIONS (mm Are The Original Dimensions) Note 1. Terminal Dimensions Within This Zone Are ... Apr 20th, 2024

## **BC546/547/548/549/550 NPN Epitaxial Silicon Transistor**

Figure 5. Output Capacitance Figure 6. Current Gain Bandwidth Product 0 2468  
101214161820 0 20 40 60 80 100 I B = 50 $\mu$ A I B = 100 $\mu$ A I B = 150 $\mu$ A I B = 200 $\mu$ A I  
B = 250 $\mu$ A I B = 300 $\mu$ A I B = 350 $\mu$ A I B = 400 $\mu$ A I C [mA], COLLECTOR CURRENT V  
CE [V], COLLECTOR-EMITTER VOLTAGE 0.0 0.2 0.4 0.6 0.8 1.0 1.2 0. Jan 11th, 2024

## **NTE130 (NPN) & NTE219 (PNP) Silicon Power Transistor ...**

Silicon Power Transistor Audio Power Amp, Medium Speed Switch Description: The  
NTE130 (NPN) And NTE219 (PNP) Are Silicon Complementary Transistors In A TO3  
Type Case Designed For General Purpose Switching And Amplifier Applications.  
Features: DC Current Gain: HFE = 20 - 70 @ IC = 4A Collector-Emitter Saturation  
Voltage: VCE(sat) = 1.1V (Max ... Apr 5th, 2024

## **MJE340 - Plastic Medium-Power NPN Silicon Transistor**

0.01 0.03 1.0 2.0 5.0 10 20 50 100 2000.1 0.50.2 1.0 0.2 0.1 R(t), Effective  
Transient 0.05 Jc(t) = R(t) Jc Jc = 3.12 $^{\circ}$ c/w Max D Curves Apply For Power Pulse  
Train Shown Read Time At T1 ... Asme Y14.5m, 1994. 2. Controlling Dimension:  
Millimeters. 3. Number And Shape Of Lugs Optional. 2x 2x Q D L1 P B2 B E C L A1 A

Front View Back View Front ... Jan 14th, 2024

### **PBSS4140DPN 40 V Low V CEsat NPN/PNP Transistor**

2001 Dec 13 5 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN/PNP Transistor PBSS4140DPN Handbook, Halfpage 0 1000 200 400 600 800 MLD642 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Mar 22th, 2024

### **PBSS4140U 40 V Low V CEsat NPN Transistor - Nexperia**

2001 Jul 13 4 NXP Semiconductors Product Data Sheet 40 V Low VCEsat NPN Transistor PBSS4140U Handbook, Halfpage 0 1000 200 400 600 800 MLD660 10-1 1 (1) 10 IC (mA) HFE 102 103 104 Jan 24th, 2024

### **NSS20201L - 20 V, 4.0 A, Low VCE(sat), NPN Transistor**

NSS20201LT1G, NSV20201LT1G [www.onsemi.com](http://www.onsemi.com) 2 MAXIMUM RATINGS (TA = 25°C) Rating Symbol Max Unit Collector-Emitter Voltage VCEO 20 Vdc Collector-Base Voltage VCBO 20 Vdc Emitter-Base Voltage VEBO 6.0 Vdc Collector Current – Continuous IC 2.0 A Collector Current – Peak ICM 4.0 A Mar 22th, 2024

### **NSS12501UW3T2G 12 V, 7.0 A, Low VCE(sat) NPN Transistor**

Electrostatic Discharge ESD HBM Class 3B MM Class C THERMAL CHARACTERISTICS  
Characteristic Symbol Max Unit Total Device Dissipation, TA = 25°C Derate Above  
25°C PD (Note 1) 875 7.0 MW MW/°C Thermal Resistance, Junction-to-Ambient R JA  
(Note 1) 143 °C/W Total Device Dissipation, TA Jan 4th, 2024

### **MPS5179 / MMBT5179 / PN5179 NPN RF Transistor**

Cover Tape Carrier Tape Note/Comments Packaging Option SOT-23 Packaging  
Information Standard (no Flow Code) D87Z Packaging Type Reel Size TNR 7" Dia  
TNR 13" Qty Per Reel/Tube/Bag 3,000 10,000 Box Dimension (mm) 187x107x183  
343x343x64 Max Qty Per Box 24,000 30,000 Weight Per Unit (gm) 0.0082 0.0082  
Weight Per Reel (kg) 0.1175 0.4006 Human ... Feb 6th, 2024

### **TOSHIBA Transistor Silicon NPN Tr Iple Diffused Type (PCT ...**

Mar 10, 2010 · Plasma Display, Nixie Tube Driver Applications Cathode Ray Tube  
Brightness Control Applications • High Breakdown Voltage: VCBO = 300 V, ... 12 14  
0.6 2 0.5 0.4 0.3 0.2 50 90 80 12 0 0 10 8 2 80 120 160 Common Emitter Ta = 25°C  
70 IB = 10 µA 20 Apr 13th, 2024

## **2N4401/MMBT4401 NPN General Purpose Amplifier**

2N4401 \*MMBT4401 PD Total Device Dissipation Derate Above 25°C 625 5.0 350  
2.8 MW MW/°C RθJC Thermal Resistance, Junction To Case 83.3 °C/W RθJA Thermal  
Resistance, Junction To Ambient 200 357 °C/W 2N4401 / MMBT4401 C B E TO-92 C  
B E SOT-23 Mark: 2X \*Device Mounted On FR-4 PCB 1.6" X 1.6" X 0.06." Discrete  
POWER & Signal Technologies Feb 7th, 2024

## **Small Signal General Purpose Transistors (NPN) 2N4400/2N4401**

2N4400/2N4401 Small Signal General Purpose Transistors (NPN )  
Www.taitroncomponents.com Page 2 Of 4 Electrical Characteristics (T  
Ambient=25°C Unless Noted Otherwise) 2N4400 2N4401 Symbol Description Min.  
Max. Min. Max. Unit Conditions V(BR)CBO Collector-Base Breakdown Voltage 60 - 60  
- V IC=100µA, IE=0 Jan 3th, 2024

## **2N4401, MMBT4401 - NPN General-Purpose Amplifier**

2N4401 / MMBT4401 Rev. 1.1.0 November 2014 2N4401 / MMBT4401 NPN General-  
Purpose Amplifier Ordering Information Figure 1. 2N4401 Device Package Figure 2.



MMBT4401 Device Package Part Number Marking Package Packing Method  
2N4401BU 2N4401 TO-92 3L Bulk 2N4401TF 2N4401 TO-92 3L Tape And Reel  
2N4401TFR 2N4401 TO-92 3L Tape And Reel 2N4401TA 2N4401 ... Mar 1th, 2024

### **LOW FREQUENCY SMD CRYSTALLLOW FREQUENCY SMD ...**

LOW FREQUENCY SMD CRYSTALLLOW FREQUENCY SMD CRYSTALOW FREQUENCY  
SMD CRYSTAL STANDARD SPECIFICATIONS: OUTLINE DRAWING: MARKING  
INSTRUCTIONS: OPTIONS AND PART IDENTIFICATION (Left Blank If Standard): 8.0 X  
3.8 X 2.5mm TABLE 1: 20.000 To 27.000 (Fund) 30 9.000 To 12.999 (Fund) 60  
13.000 To 15.999 ... Mar 6th, 2024

### **Smd Transistor Code Wordpress**

Size Chart - Footprint Selection Chart - TopLine Dummy 40 V, 200 MA NPN Switching  
Transistor 5 November 2020 Product Data Sheet 1. General Description NPN  
Switching Transistor In A Small SOT23 (TO-236AB) Surface-Mounted Feb 15th, 2024

### **Smd Transistor Marking Code Pdf - Mbmwebsite.com**

SMD Code Book And Marking Codes - ElectroSchematics.com Next Look Up The

Code In The Alphanumeric Listing Which Forms The Main Part Of The Pdf Book By Looking For The First Character In The Left Column. You Can Use The CTRL + F Shortcut To Search For A ... Feb 9th, 2024

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